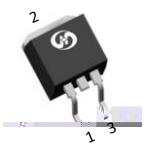
80V N-Ch Power MOSFET

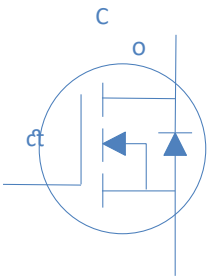
ct ct
F ctct ct
ct w ct w
ct ct ct ct
44 Sct ct 44 Sct ct
ct ctct F ct ctct

V_{DS}		80	V
$R_{DS(on),typ}$	TO-263	2.6	m
$R_{DS(on),typ}$	TO-220	2.9	m
$I_{D\ (Sillicon\ Limited)}$		182	A
$I_{D\ (Package\ Limited)}$		120	A

w ct L
F F ctct
C C Sctct l

S /o0 S /oo4





Part Number	Package	Marking
HGB028N08A	TO-263	GB028N08A
HGP028N08A	TO-220	GP028N08A

Absolute Maximum Ratings at T_j=25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current(Silicon Limited)	I_D	T_C=25℃	182	A
		T_C=100℃	128	
Continuous Drain Current(Package Limited)		T_C=25℃	120	
Drain to Source Voltage	V_{DS}	-	80	V
Gate to Source Voltage	V_{GS}	-	±20	V
Pulsed Drain Current	I_{DM}	-	520	A
Avalanche Energy, Single Pulse	E_{AS}	L=0.4mH, T_C=25℃	720	mJ
Power Dissipation	P_D	T_C=25℃	200	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to175	℃

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	R_{JA}	50	℃/W
Thermal Resistance Junction-Case	R_{JC}	0.75	℃/W

Electrical Characteristics at T_j=25℃ (unless otherwise specified)

Static Characteristics

Parameter	Symbol	Conditions		Value			Unit
				min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250 A		80	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250 A		2.0	2.7	4.0	
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V, V_{DS}=80V, T_j=25℃		-	-	1	A
		V_{GS}=0V, V_{DS}=80V, T_j=100℃		-	-	100	
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V		-	-	±100	nA
Drain to Source on Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A	TO-263	-	2.6	3.1	m
Drain to Source on Resistance		V_{GS}=10V, I_D=20A	TO-220	-	2.9	3.4	m
Transconductance	g_{fs}	V_{DS}=5V, I_D=20A		-	70	-	S
Gate Resistance	R_G	V_{GS}=0V, V_{DS} Open, f=1MHz		-	0.5	-	

Dynamic Characteristics

Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=40V, f=1MHz	-	5386	-	pF
Output Capacitance	C_{oss}		-	1003	-	
Reverse Transfer Capacitance	C_{rss}		-	38	-	
Total Gate Charge	Q_g(10V)	V_{DD}=40V, I_D=20A, V_{GS}=10V	-	105	-	nC
Gate to Source Charge	Q_{gs}		-	20	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	36	-	
Turn on Delay Time	$t_{d(on)}$	V_{DD}=40V, I_D=20A, V_{GS}=10V, R_G=10 ,	-	23	-	ns
Rise time	t_r		-	19	-	
Turn off Delay Time	$t_{d(off)}$		-	38	-	
Fall Time	t_f		-	12	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_F=20A	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R=40V, I_F=20A, dI_F/dt=100A/ s	-	62	-	ns
Reverse Recovery Charge	Q_{rr}		-	94	-	nC

Fig 1. Typical Output Characteristics

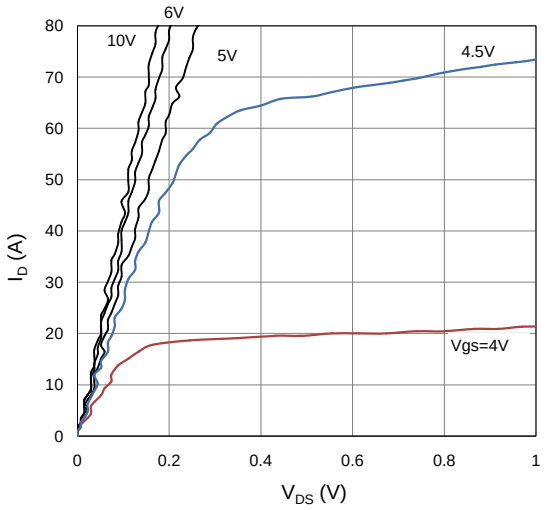


Figure 2. On-Resistance vs. Gate-Source Voltage

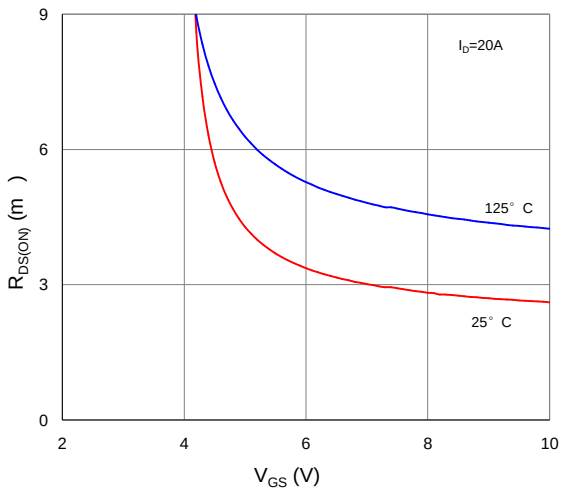


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

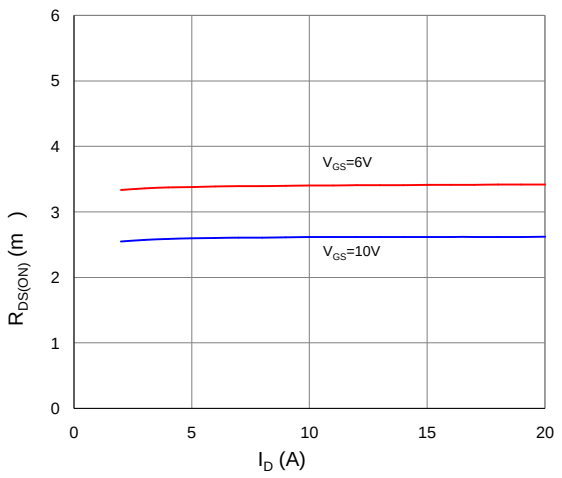


Figure 4. Normalized On-Resistance vs. Junction Temperature

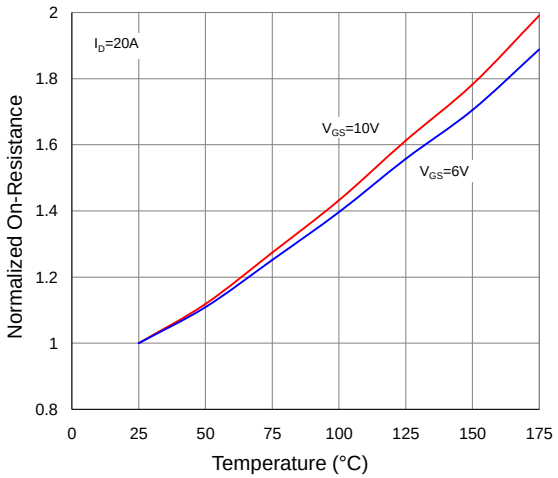


Figure 5. Typical Transfer Characteristics

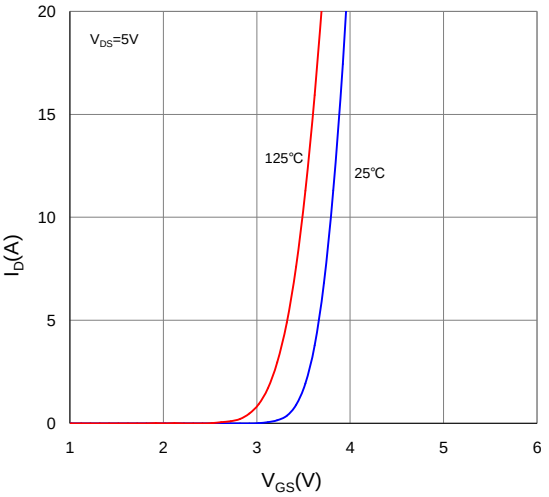


Figure 6. Typical Source-Drain Diode Forward Voltage

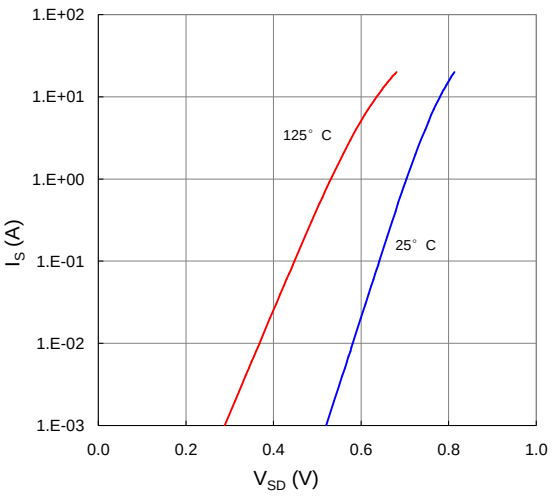


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

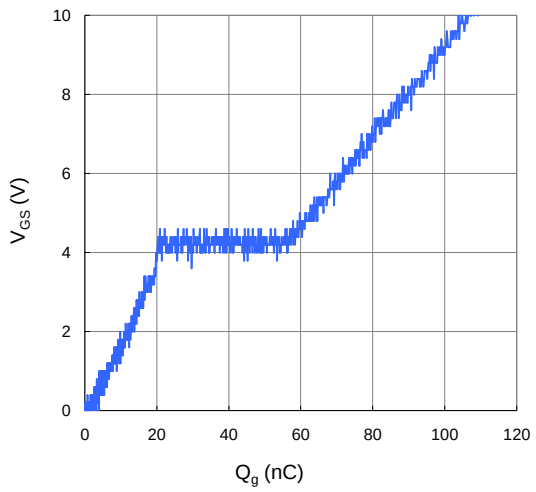


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

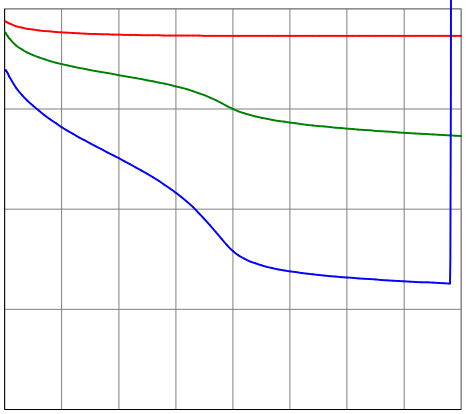
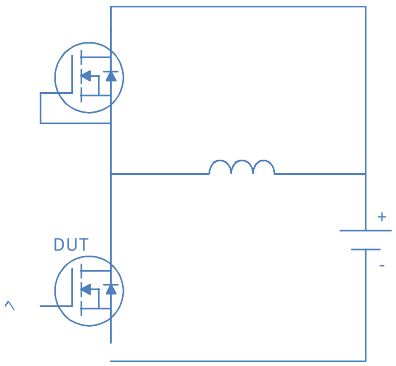


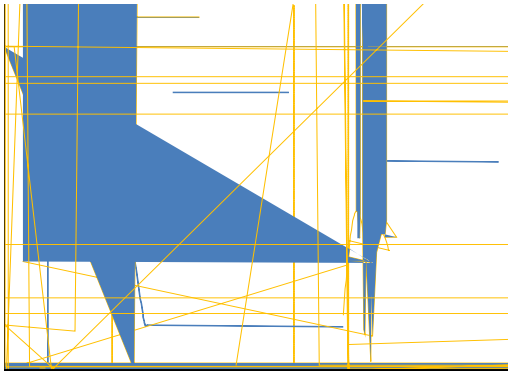
Figure 9. Maximum Safe Operating Area

Figure 10. Maximun Drain Current vs. Case Temperature

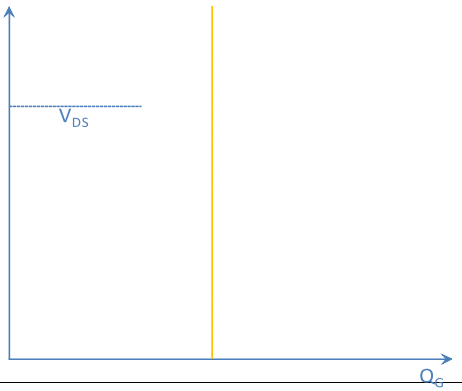
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

Inductive switching Test

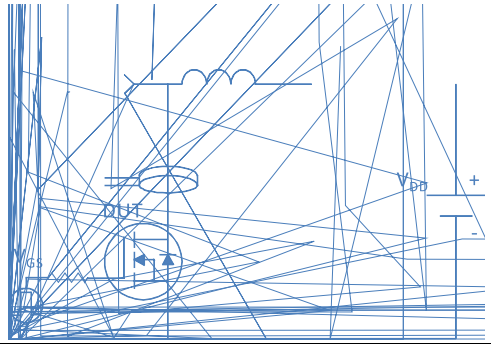


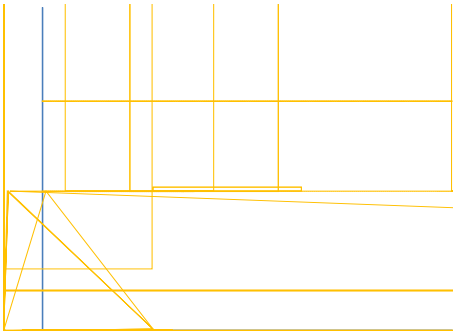


Gate Charge Test

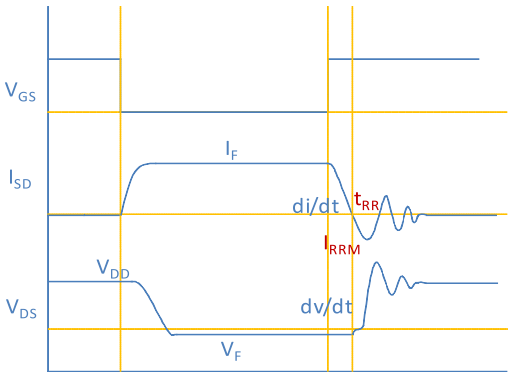


Uclamped Inductive Switching (UIS) Test



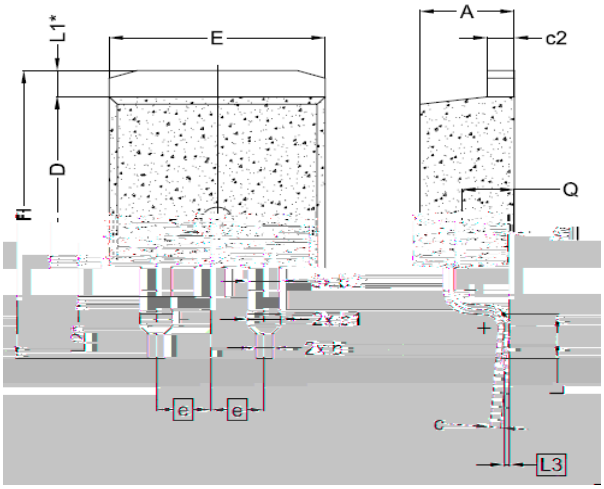


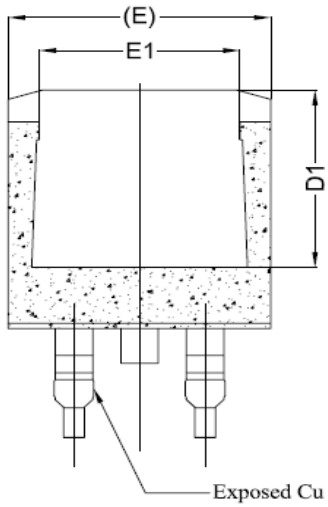
Diode Recovery Test



Package Outline

TO-263, 2 leads

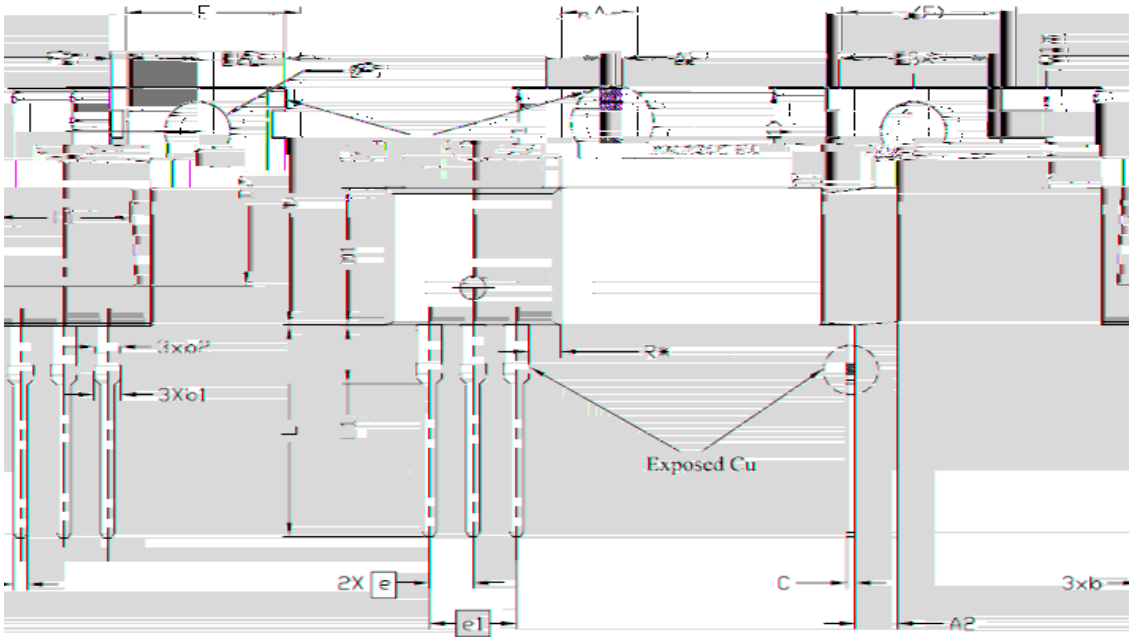




SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86		7.65
		E	
	7.59	E1	
		e	2.54
		H	
		L	
		L1	
		L2	
		L3	
		Q	

Package Outline

TO-220, 3 leads



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.24	4.44	4.64	
A1	1.15	1.27	1.40	
A2	2.30	2.48	2.70	
b	0.70	0.80	0.90	
b1	1.20	1.55	1.75	
b2	1.20	1.45	1.70	
c	0.40	0.50	0.60	
D	14.70	15.37	16.00	4
D1	8.82	8.92	9.02	
D2	12.63	12.73	12.83	5
E	9.96	10.16	10.36	4,5
E1	6.86	7.77	8.89	5
E2	-	-	0.76	6
E3*	8.70REF.			
e	2.54BSC			
e1	5.08BSC			
H1	6.30	6.45	6.60	5,6
L	13.47	13.72	13.97	
L1	3.60	3.80	4.00	
ØP	3.75	3.84	3.93	
Q	2.60	2.80	3.00	
Q1*	1.73REF.			
R*	1.82REF.			